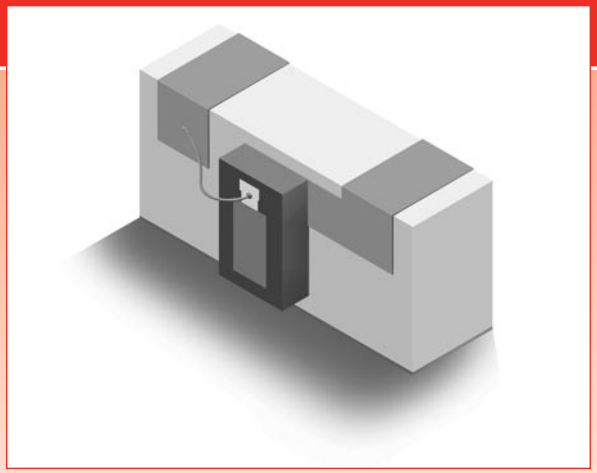
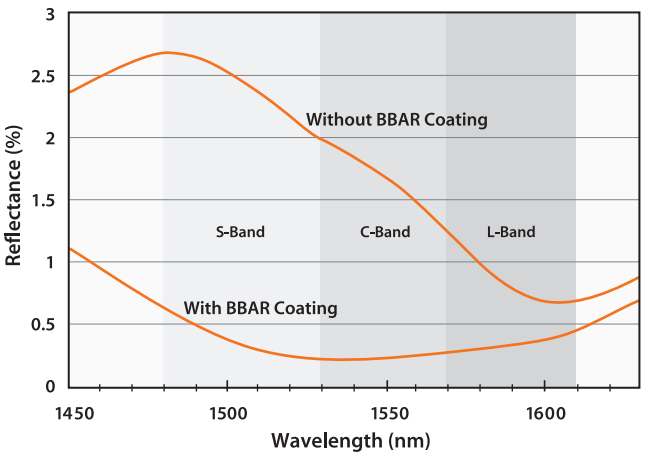
FCI-InGaAs-WCER-LR

Broadband Anti-Reflection Coated InGaAs Photodiodes

OSI Optoelectronics's latest product line includes a very low reflectance photodiode. Designed for telecommunication applications, the InGaAs/InP photodiode has a typical optical reflectance of less than .6% from 1520nm to 1620nm. This ultra low reflectance over the wide wavelength range was achieved by depositing a proprietary multi-layered Anti-Reflection coating directly onto the surface of the InGaAs/InP photodiode.



Reflectance Curve

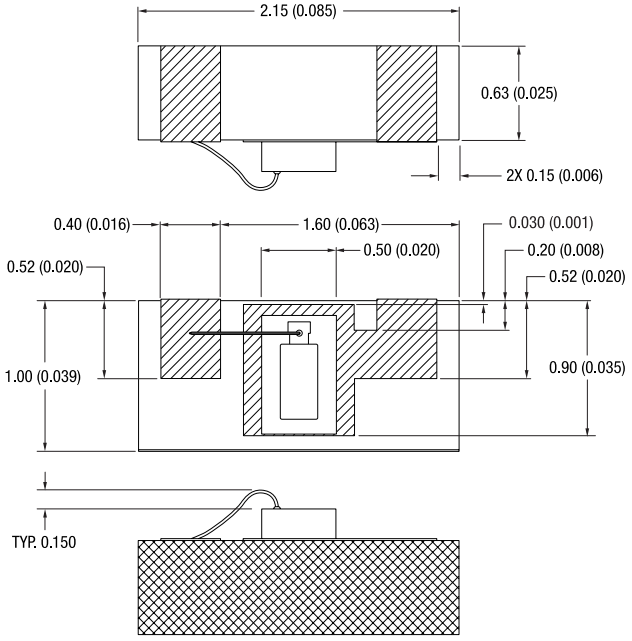


APPLICATIONS

- Wavelength Locker / Wavelength Monitoring
- Lasers Back Facet Monitoring
- DWDM
- Instrumentation

FEATURES

- Reflectance Less than 0.6%
- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm



Absolute Maximum Ratings

PARAMETERS	SYMBOL	MIN	MAX	UNITS
Storage Temperature	T_{stg}	-40	+85	°C
Operating Temperature	T_{op}	0	+70	°C
Soldering Temperature	T_{sld}	---	+260	°C

Electro-Optical Characteristics T_A=23°C

PARAMETERS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	AA	---	---	250X500	---	µm X µm
Responsivity	R_λ	λ = 1310nm	0.85	0.90	---	A/W
		λ = 1550nm	0.90	0.95	---	
Capacitance	C_j	V_R=5.0V	---	15	---	pF
Dark Current	I_d	V_R=5.0V	---	---	1	nA
Max. Reverse Voltage	---	---	---	---	20	V
Max. Reverse Current	---	---	---	---	2	mA
Max. Forward Current	---	---	---	---	5	mA
Reflectance	---	1520nm≤ λ ≤1620nm	---	0.5	0.6	%

Notes:
- All units in millimeters.
- All devices are mounted with low out gassing conductive epoxy withtolerance of ±25µm. Eutectic mounting is also availabel upon request.

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